

ABSTRACT

A semiconductor device includes a semiconductor substrate, a polysilicon pattern formed
5 on the semiconductor substrate via an insulation film, an interlayer insulation film formed on the semiconductor substrate so as to cover the polysilicon pattern, and a metal interconnection layer pattern formed on the interlayer insulation
10 film, wherein the metal interconnection layer pattern carrying silicon nitride films respectively on a top surface, a bottom surface and sidewall surfaces thereof.